UMBT-STB110BS SURGE SUPPRESSOR BRIDGE

FEATURES:

- RoHS compliant
- Lower clamping voltage and excellent performance on ringing waves testing.
- · Lead Free Finish/RoHS Compliant
- Green Molding Compound (No Halogen and Antimony)
- Glass Passivated Chip Junction
- · High Surge Current Capability
- Designed for Surface Mount Application

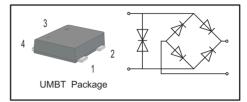
MECHANICAL DATA

• Case: UMBT

Terminals: Solderable per MIL-STD-750, Method 2026
Approx. Weight: 60mg/0.0021oz

PINNING

PIN	DESCRIPTION		
1	Input Pin (~)		
2	Input Pin (~)		
3	Output Anode (+)		
4	Output Cathode (-)		



Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	STB110BS	
Average Rectified Output Current @ Fig.1	Io	1.0	А
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I _{FSM}	30	А
Maximum Forward Voltage at 1.0 A	V _F	1.1	V
	I _R	5 40	μA
Typical Junction Capacitance (Note1)	Cj	7	pF
Typical Thermal Resistance (Note2)	$R_{ heta JA} \ R_{ heta JC} \ R_{ heta JL}$	45 10 25	°C/W
Operating and Storage Temperature Range	T_j, T_{stg}	-55 ~ + 150	°C

Note: 1. Measured at 1MHz and applied reverse voltage of 4 V D.C.

2. Mounted on glass epoxy PC board with 4×1.5"×1.5" (3.81×3.81 cm) copper pad.

Maximum Ratings and Thermal Characteristics(TA = 25°C unless otherwise specified)

Technology Data		STB110BS	Unit
Maximum allowable continuous AC voltage at 50-60Hz	V_{RMS}	125	V
Breakdown Voltage at 1mA	$V_{\mathtt{BR}}$	190~240	V
Maximum allowable continuous DC voltage	V _{DC}	170	V
Maximum allowable clamping voltage	V _C	300	٧
Maximum peak current (8/20μs@2Ω)	I _{peak}	200	А
Operating Junction Temperature and Storage Temperature Range	T_{j}, T_{stg}	-55 ~ +150	°C

NOTES

- 1. The breakdown voltage was measured at 1mA
- 2. The clamping voltage was measured at 8/20µs standard current, (1A)
- 3. The peak current was tested at 8/20µs waveform

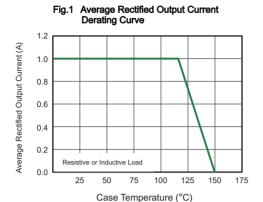


Fig.3 Typical Instaneous Forward Characteristics

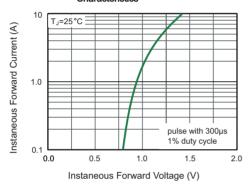


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

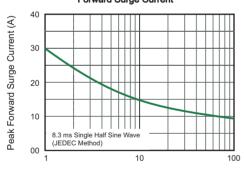


Fig.7 Peak Pulse Power Rating Curve

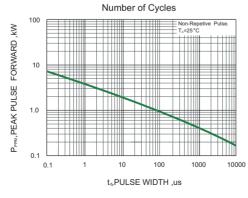


Fig.2 Typical Reverse Characteristics

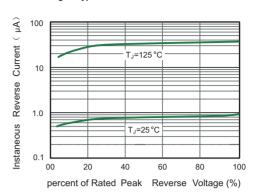


Fig.4 Typical Junction Capacitance

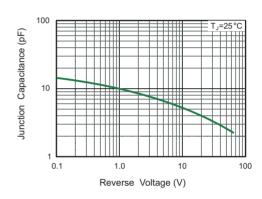
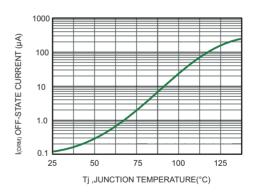
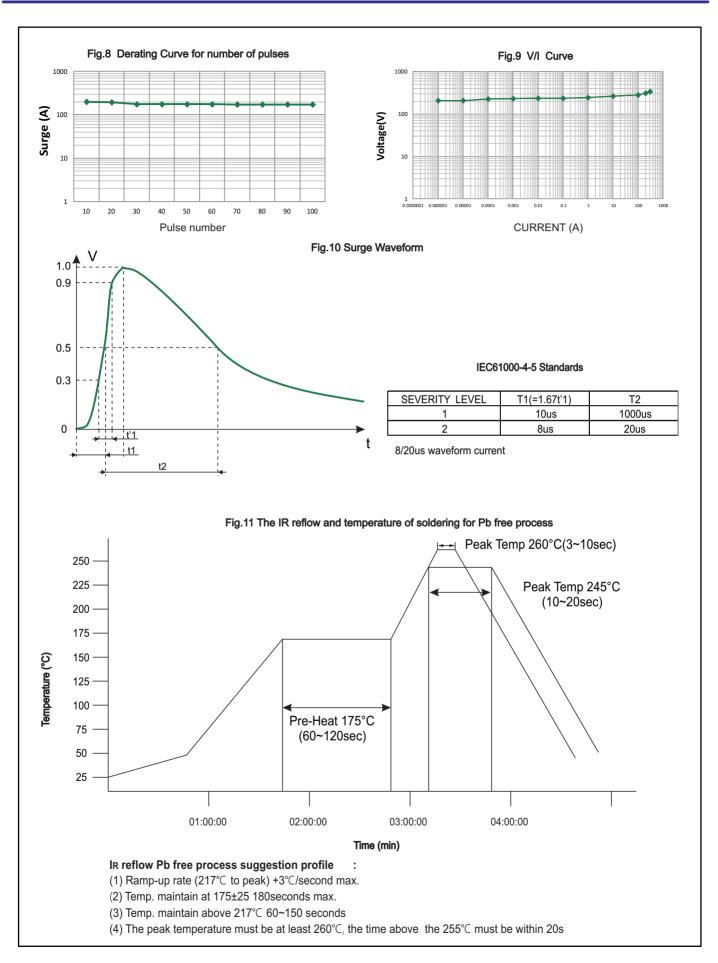


Fig.6 Off-State Current vs. Junction Temperature

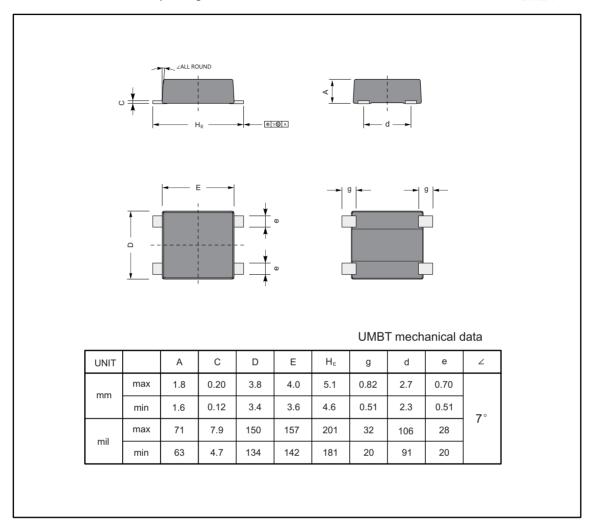




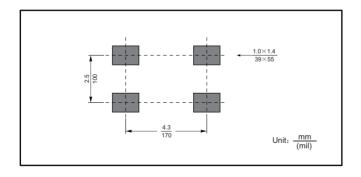
PACKAGE OUTLINE

Plastic surface mounted package; 4 leads

UMBT

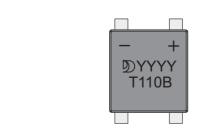


The recommended mounting pad size



Marking

Type number	Marking code	
STB110BS	T110B	



MARKING DIAGRAM

- 1. T110B: Marking content;
- 2. YYYY: Four digit traceability code;
- 3. D: LOGO of Jingdao;
- 4. +: Anode symbol;
- 5. -: Cathode symbol;

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